

## Method of manufacturing a semiconductor device

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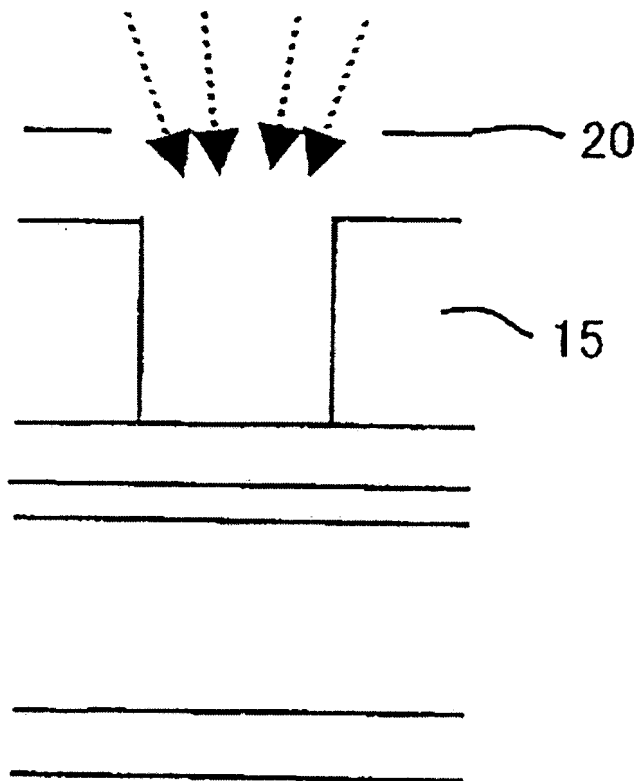
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### Abstract of TW511188B

A method of manufacturing a semiconductor device provided with a first insulating film and a barrier film on a conductive region and an opening portion in the first insulating film and the barrier film, the method comprising the steps of: forming a first opening portion in the barrier film reaching the first insulating film; forming a second insulating film at least on the first insulating film in the first opening portion; and forming a second opening portion smaller than the first opening portion and reaching the conductive region by simultaneously boring a hole into the first insulating film and the second insulating film in the first opening portion.



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